

STARPOWER

SEMICONDUCTOR

Rectifier Diode

RD160FFS180K2S

Molding Type Module

1800V/160A 6 in one-package

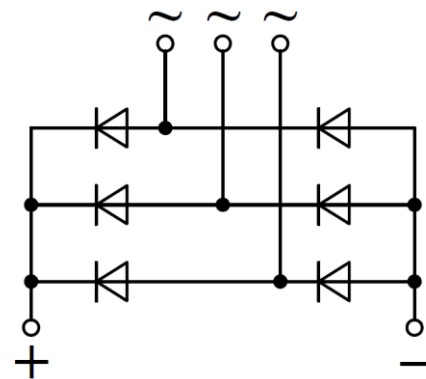


General Description

STARPOWER Rectifier Diode Power Module provides ultra low conduction loss. They are designed for the applications such as SMPS.

Features

- Low forward voltage drop
- Small temperature coefficient
- High Surge Capacity
- Low inductance
- Isolated Copper Baseplate Using DBC Technology



Equivalent Circuit Schematic

Typical Applications

- Input bridge rectifier
- AC/DC motor control
- Power supply

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Description	RD160FFS180K2S	Units
V_{RRM}	Repetitive Peak Reverse Voltage	1800	V
V_{RSM}	Non-repetitive Peak Reverse Voltage	1800	V
I_{FAV}	Average Forward Current $T_C=100^\circ\text{C}$	160	A
I_{FSM}	Surge Forward Current $V_R=0\text{V}, t_p=10\text{ms}, T_j=45^\circ\text{C}$	1800	A
	$V_R=0\text{V}, t_p=8.3\text{ms}, T_j=45^\circ\text{C}$	1850	
I^2t	I^2t -value $V_R=0\text{V}, t_p=10\text{ms}, T_j=45^\circ\text{C}$	16200	A^2s
	$V_R=0\text{V}, t_p=8.3\text{ms}, T_j=45^\circ\text{C}$	14260	
P_D	Maximum Power Dissipation @ $T_j=150^\circ\text{C}$	286	W
T_j	Junction Temperature	-40 to +150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^\circ\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	4000	V
M	Terminal Connection Torque, Screw M6	2.5 to 5.0	N.m
	Mounting Torque, Screw M6	3.0 to 5.0	

Electrical Characteristics of Diode $T_C=25^\circ\text{C}$ unless otherwise noted

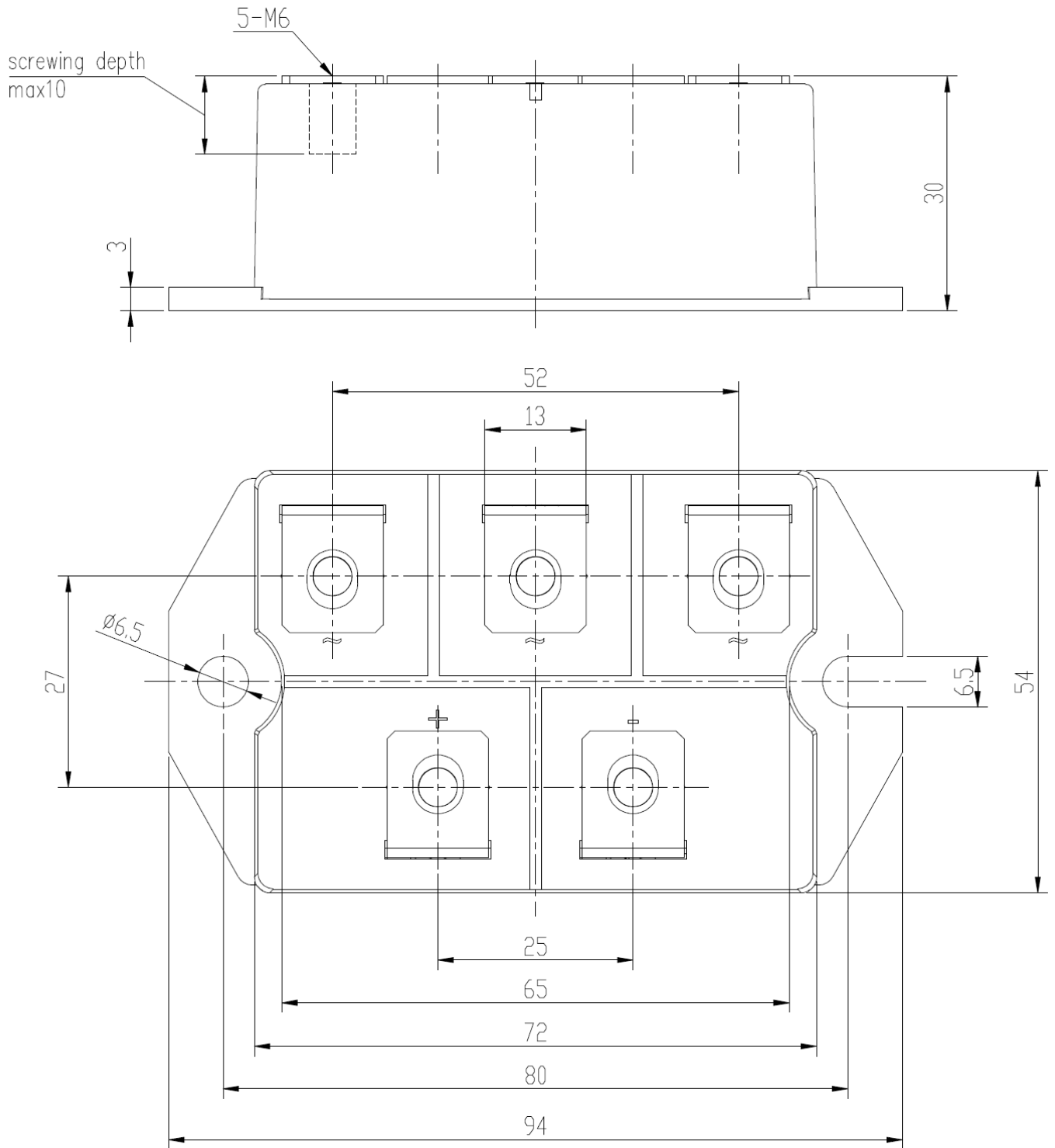
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	$I_F=200\text{A}$	$T_j=25^\circ\text{C}$		1.25	V
			$T_j=150^\circ\text{C}$		1.20	
V_F	Threshold Voltage	$T_j=150^\circ\text{C}$			0.86	V
r_T	Forward Slope Resistance	$T_j=150^\circ\text{C}$			1.7	$\text{m}\Omega$
I_R	Diode Reverse Current	$V_R=V_{RRM}$	$T_j=25^\circ\text{C}$		0.05	mA
			$T_j=150^\circ\text{C}$		2.00	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (per Diode)		0.437	K/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.03		K/W
Weight	Weight of Module	270		g

Package Dimensions

Dimensions in Millimeters



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